

09/666156  
JCE93 U.S. PRO

Class	Subclass	Issue Classification

**PATENT NUMBER**

**U.S. UTILITY Patent Application**

O.I.P.E.

**PATENT DATE**

AC-  
SCANNED 

84

478

APPLICATION NO. 09/666156	CONT/PRIOR F	CLASS 257	SUBCLASS 335	ART UNIT 2811	EXAMINER Lowe Thomas
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## APPlicants

Haruko Inoue  
Yuichi Kitamura

TIME

## High-voltage MOS transistor and method for fabricating the same

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## **ISSUING CLASSIFICATION**

<input type="checkbox"/> <b>TERMINAL DISCLAIMER</b>	<b>DRAWINGS</b>			<b>CLAIMS ALLOWED</b>	
	Sheets Drwg.	Figs. Drwg.	Print Fig.	Total Claims	Print Claim for O.G.
<input type="checkbox"/> The term of this patent subsequent to _____ (date) has been disclaimed.				<b>NOTICE OF ALLOWANCE MAILED</b>	
				(Assistant Examiner)	(Date)
<input type="checkbox"/> The term of this patent shall not extend beyond the expiration date of U.S Patent. No. _____ _____ _____				<b>ISSUE FEE</b>	
				(Primary Examiner)	(Date)
<input type="checkbox"/> The terminal _____ months of this patent have been disclaimed.				<b>ISSUE BATCH NUMBER</b>	
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